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PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10008204	12/05/2001	438		2812	13-202

\*\*APPLICANTS: Chern Geeng-Chuan; Levi Amitay; Lee Dana;

\*\*CONTINUING DATA VERIFIED:

\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed		<input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO
35 USC 119 conditions met		<input type="checkbox"/> yes <input type="checkbox"/> no	2102397-991220
Verified and Acknowledged Examiner's initials			
TITLE : Method of forming different oxide thickness for high voltage transistor and memory cell tunnel dielectric			
U.S. DEPT. OF COMM./PAT. & TM-FTO-436L(Rev. 12-94)			

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	
		Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.
		Print Fig.	
TERMINAL DISCLAIMER		Primary Examiner	
		PREPARED FOR ISSUE	
		Application Examiner	
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